

General Description

The WSP3099 is the highest performance trench P-Ch MOSFET with extreme high cell density , which provide excellent RDSON and gate charge for most of the synchronous buck converter applications .

The WSP3099 meet the RoHS and Green Product requirement with full function reliability approved.

Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- Green Device Available

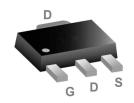
Product Summery

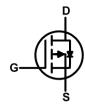
BVDSS	RDSON	ID
-30V	53mΩ	-5.0A

Applications

- High Frequency Point-of-Load Synchronous Buck Converter for MB/NB/UMPC/VGA
- Networking DC-DC Power System
- Load Switch

SOT-89 Pin Configuration





Absolute Maximum Ratings

Symbol	Parameter Rating		Units
V_{DS}	Drain-Source Voltage	-30	V
V_{GS}	Gate-Source Voltage	±20	V
I _D @T _C =25℃	Continuous Drain Current, -V _{GS} @ -10V ¹	-5.0	Α
I _D @T _C =100℃	Continuous Drain Current, -V _{GS} @ -10V ¹ -4.0		Α
I _{DM}	Pulsed Drain Current ²	-20	А
EAS	Single Pulse Avalanche Energy ³	18	mJ
I _{AS}	Avalanche Current	8	Α
P _D @T _C =25℃	Total Power Dissipation⁴	1.8	W
T _{STG}	Storage Temperature Range	-55 to 150	$^{\circ}\!\mathbb{C}$
T_J	Operating Junction Temperature Range	-55 to 150	℃

Thermal Data

Symbol	Parameter	Тур.	Max.	Unit
R _{0JA}	Thermal Resistance Junction-Ambient ¹		62.5	°C/W
$R_{ heta JC}$	Thermal Resistance Junction-Case ¹		30	°C/W



Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V , I _D =-250uA	-30			V
$\triangle BV_{DSS}/\triangle T_{J}$	BVDSS Temperature Coefficient	Reference to 25℃, I _D =-1mA		-0.02		V/°C
В	Static Drain-Source On-Resistance ²	V _{GS} =-10V , I _D =-5.0A		53	65	mΩ
R _{DS(ON)}		V _{GS} =-4.5V , I _D =-3.8A		80	98	
$V_{GS(th)}$	Gate Threshold Voltage	V _{GS} =V _{DS} . In =-250uA	-1.0	-1.5	-2.0	٧
$\triangle V_{GS(th)}$	V _{GS(th)} Temperature Coefficient	W _{GS} =V _{DS} , I _D =-2500A		4.32		mV/℃
	Drain Source Leakage Current	V_{DS} =-24V , V_{GS} =0V , T_J =25 $^{\circ}$ C			-1	
I _{DSS}	Drain-Source Leakage Current	V _{DS} =-24V , V _{GS} =0V , T _J =55℃			-5	uA
I _{GSS}	Gate-Source Leakage Current	V_{GS} = $\pm 20V$, V_{DS} = $0V$			±100	nA
gfs	Forward Transconductance	V_{DS} =-5 V , I_{D} =-3 A		5.5		S
Rg	Gate Resistance	V _{DS} =0V , V _{GS} =0V , f=1MHz		24	48	Ω
Q_g	Total Gate Charge (-4.5V)	V _{DS} =-15V , V _{GS} =-4.5V , I _D =-5A		11.6		
Q_gs	Gate-Source Charge			1.3		nC
Q _{gd}	Gate-Drain Charge			2.5		
T _{d(on)}	Turn-On Delay Time			6	12	
T _r	Rise Time	V_{DD} =-15V, V_{GEN} =-10V, R_{G} =3.3 Ω		12	23	ns
T _{d(off)}	Turn-Off Delay Time	I_D =-1A ,RL=15 Ω		25	46	
T _f	Fall Time			6	12	
Ciss	Input Capacitance	V _{DS} =-15V , V _{GS} =0V , f=1MHz		625		
C _{oss}	Output Capacitance			100		pF
C _{rss}	Reverse Transfer Capacitance			60		

Guaranteed Avalanche Characteristics

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
EAS	Single Pulse Avalanche Energy ⁵	V _{DD} =25V , L=0.1mH , I _{AS} =6A	6			mJ

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
I _S	Continuous Source Current ^{1,6}	-V _G =V _D =0V , Force Current			-2.0	Α
I _{SM}	Pulsed Source Current ^{2,6}				-20	Α
V _{SD}	Diode Forward Voltage ²	V _{GS} =0V , I _S =-1.7A , T _J =25℃			-1	V

Note

- 1. The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper,t<10sec.
- 2.The data tested by pulsed , pulse width \leq 300us , duty cycle \leq 2%
- 3. The EAS data shows Max. rating . The test condition is V_{DD} =-25V, V_{GS} =-10V, L=0.1mH, I_{AS} =-6A
- 5.The Min. value is 100% EAS tested guarantee.
- 6. The data is theoretically the same as I_D and I_{DM} , in real applications, should be limited by total power dissipation.



Typical Characteristics

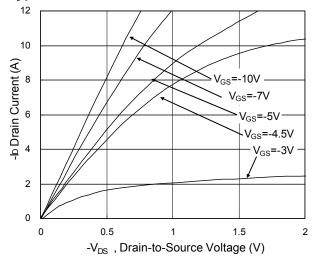
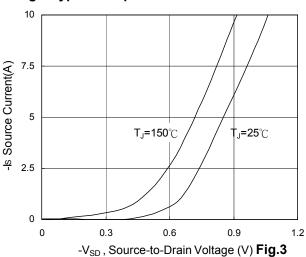


Fig.1 Typical Output Characteristics



Forward Characteristics of Reverse

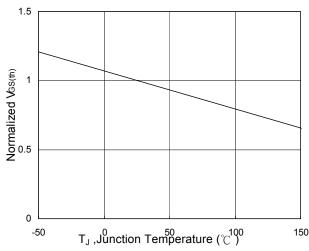


Fig.5 Normalized V_{GS(th)} vs. T_J

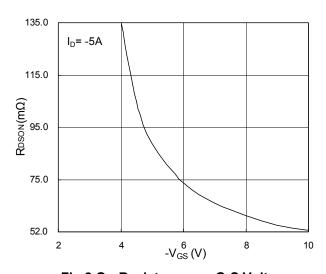


Fig.2 On-Resistance vs. G-S Voltage

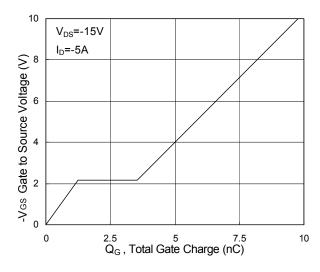


Fig.4 Gate-Charge Characteristics

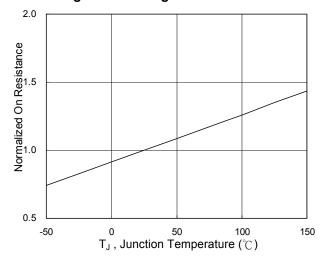
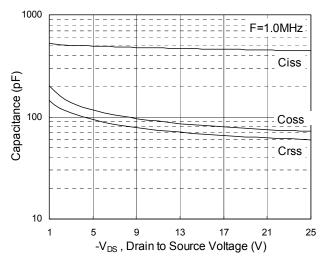


Fig.6 Normalized R_{DSON} vs. T_J





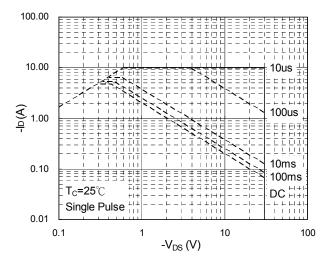


Fig.7 Capacitance

Fig.8 Safe Operating Area

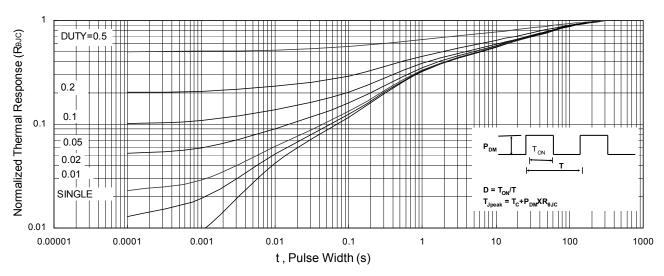


Fig.9 Normalized Maximum Transient Thermal Impedance

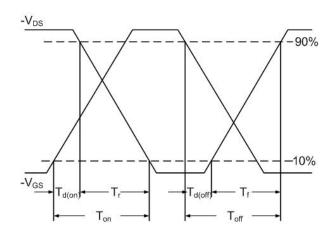


Fig.10 Switching Time Waveform

Fig.11 Unclamped Inductive Waveform



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